



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

KTA1273 TRANSISTOR (PNP)

FEATURES

Power dissipation

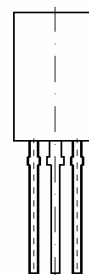
P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

TO-92L

1. EMITTER

2. COLLECTOR

3. BASE



1 2 3

MAXIMUM RATINGS* $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Dissipation	1	W
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=-1mA, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-500mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-30mA$			-2.0	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2V, I_C=-500mA$			-1.0	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-500mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		48		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320

Typical Characteristics

KTA1273

